

Silicon Carbide Schottky Diode

General Description

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.

Features

- Low conduction loss due to low VF
- Extremely low switching loss by tiny Qc
- Highly rugged due to better surge current
- Industrial standard quality and reliability

Applications

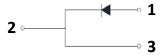
- UPS
- Power Inverter
- High performance SMPS
- Power factor correction

| Ordering Part Number | Package | Qty(PCS) | |
|-------------------------|------------|----------|--|
| HIDH08G65C5XKSA2 | TO-220H-2L | 50 | |









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Maximum Ratings (at Tj = 25 °C, unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|--|--------|---------------|------|
| Repetitive Peak Reverse Voltage | Vrrm | 650 | V |
| Surge Peak Reverse Voltage | Vrsm | 650 | V |
| DC Peak Reverse Voltage | VR | 650 | V |
| Continuous Forward Current | | | |
| Tc = 25°C Tc = 135°C Tc = 160°C | lF | 30 15 8 | А |
| Repetitive Peak Forward Surge Current $T_{C} = 25^{\circ}C, t_{p} = 10 \text{ms}, \text{Half Sine Pulse}$ $T_{C} = 110^{\circ}C, t_{p} = 10 \text{ms}, \text{Half Sine Pulse}$ | lfRM | 38 25 | А |
| Non-Repetitive Forward Surge Current $T_C = 25^{\circ}C, t_P = 10 \text{ms}, Half Sine Pulse }$ $T_C = 110^{\circ}C, t_P = 10 \text{ms}, Half Sine Pulse}$ | Ігѕм | 64 53 | А |
| i^2 dt value $T_C = 25^{\circ}C, t_P = 10 ms, Half Sine Pulse T_C = 110^{\circ}C, t_P = 10 ms, Half Sine Pulse$ | ∫ i²dt | 20.5 14 | A²s |
| Power dissipation $Tc = 25^{\circ}C$ $Tc = 110^{\circ}C$ | Ptot | 93 40 | W |
| Operating junction Range | Tj | -55 to +175 | °C |
| Storage temperature Range | Tstg | -55 to +150 | °C |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--------------------------------------|--------|-------|------|
| Thermal resistance, junction - case. | RthJC | 1.60 | °C/W |



Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

| Parameter | Symbol | | Value | | Unit | Test Condition | |
|-------------------------|----------|------|-------|------|-------|--|--|
| 1 diametei | Cyllibol | min. | typ. | max. | Oilit | | |
| | | | | | | I=8A | |
| Forward Voltage | VF | - | 1.3 | 1.5 | V | T _j =25°C | |
| | | - | 1.55 | - | | Tj=175°C | |
| | | | | | | Vr=650V | |
| Reverse Current | lr | - | - | 50 | μΑ | T _j =25°C | |
| | | - | - | 200 | | T _j =175°C | |
| | | | | | | V _R =400V,T _j =25℃ | |
| Total Capacitive Charge | Qc | - | 23 | - | nC | $Q_C = \int_0^{V_R} C(V) dV$ | |
| | | | | | | Tj=25℃, f=1MHz | |
| Total Capacitance | С | - | 466 | - | pF | V _R =0V | |
| | | - | 47 | - | | V _R =200V | |
| | | - | 38 | - | | V _R =400V | |

Characteristics Curve:

Fig 1: Forward Characteristics

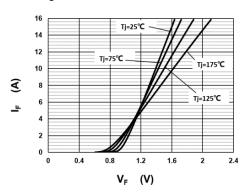


Fig 3: Current Derating

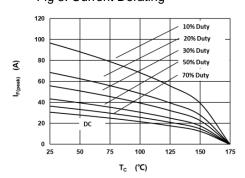


Fig 2: Reverse Characteristics

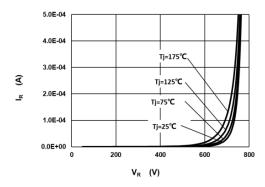
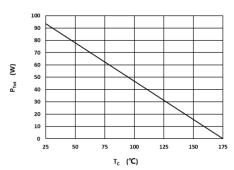


Fig 4: Power Derating



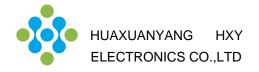


Fig 5: Capacitance vs. Reverse Voltage

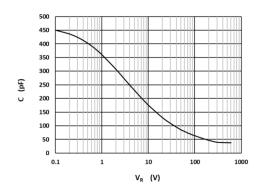


Fig 6: Reverse Charge vs. Reverse Voltage

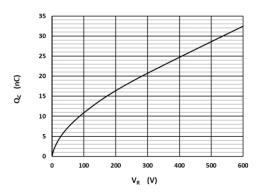


Fig 7: Typical Capacitance Stored Energy

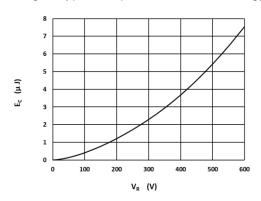
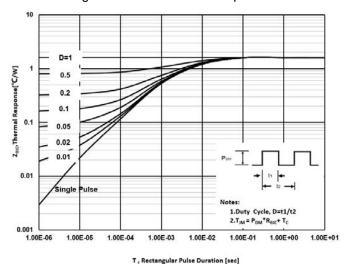
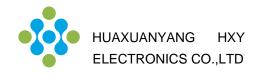
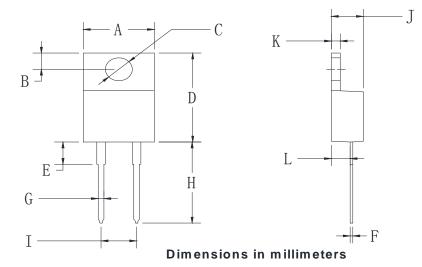


Fig 8: Transient Thermal Impandance





Package Information TO-220H-2L



| TO-220H-2L | | | |
|------------|-------|-------|--|
| Dim | Min | Max | |
| Α | 9.5 | 10.9 | |
| В | 2.22 | 3.27 | |
| С | 3.34 | 4.31 | |
| D | 14.5 | 15.5 | |
| Е | 3.16 | 4.46 | |
| F | 0.28 | 0.64 | |
| G | 0.68 | 0.94 | |
| Н | 13.06 | 14.62 | |
| I | 4.55 | 5.60 | |
| J | 4.04 | 5.1 | |
| K | 1.14 | 1.4 | |
| L | 2.14 | 3.19 | |

HIDH08G65C5XKSA2

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